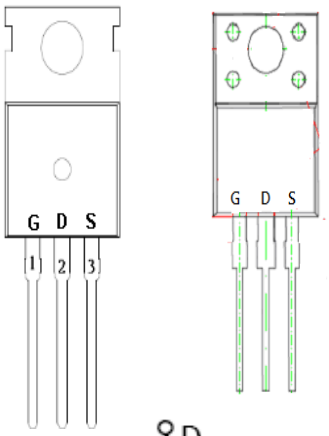
SPN120T15
N-Channel Enhancement Mode MOSFET

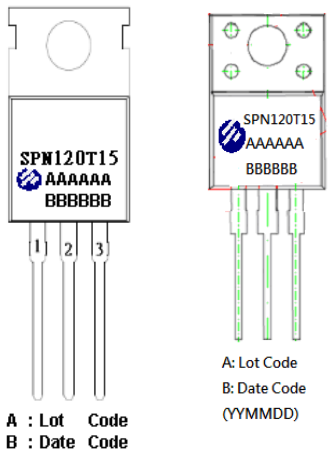
DESCRIPTION
The SPN120T15 is the N-Channel enhancement mode power field effect transistor which is produced using super high cell density DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suitable for synchronous rectifier application, Motor control power management and other Power Tool circuits. It has been optimized for low gate charge, low $R_{DS(ON)}$ and fast switching speed.

APPLICATIONS
- AC/DC Synchronous Rectifier
- Load Switch
- UPS
- Power Tool
- Motor Control

FEATURES
- 150V/120A, $R_{DS(ON)}$=10.5mΩ@V_{GS}=10V
- High density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- TO-220-3L/TO-220F-3L package design

PIN CONFIGURATION
TO-220 **TO-220F**



PART MARKING


SPN120T15
N-Channel Enhancement Mode MOSFET

PIN DESCRIPTION

Pin	Symbol	Description
1	G	Gate
2	D	Drain
3	S	Source

ORDERING INFORMATION

Part Number	Package	Part Marking
SPN120T15T220TGB	TO-220-3L	SPN120T15
SPN120T15T220FTGB	TO-220F-3L	SPN120T15

※ SPN120T15T220TGB : Tube ; Pb – Free ; Halogen – Free
※ SPN120T15T220FTGB : Tube ; Pb – Free ; Halogen - Free

ABSOULTE MAXIMUM RATINGS

(T_A=25℃ Unless otherwise noted)

Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	150	V
Gate –Source Voltage		V_{GSS}	±20	V
Continuous Drain Current(T_J=150℃)	T_C=25℃	I_D	120	A
	T_C=100℃		85	
Pulsed Drain Current		I_{DM}	400	A
Avalanche Energy, Single Pulse @ L=1mH, T_C=25℃		E_{AS}	540	mJ
Power Dissipation @ T_C=25℃		P_D	333	W
Operating Junction Temperature		T_J	-55/175	℃
Storage Temperature Range		T_{STG}	-55/175	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	60	℃/W
Thermal Resistance-Junction to Case		$R_{\theta JC}$	0.45	℃/W

SPN120T15
N-Channel Enhancement Mode MOSFET

ELECTRICAL CHARACTERISTICS

(T_A=25℃ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=250uA	150			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA	2.0		4.0	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=150V,V_{GS}=0V T_J=25℃			1	uA
		V_{DS}=150V,V_{GS}=0V T_J=100℃			100	
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V,I_D=20A		8.8	10.5	mΩ
Forward Transconductance	gfs	V_{DS}=5V,I_D=20A		90		S
Gate Resistance	R_G	V_{GS}=0V,V_{DS}=Open, f=1MHz		0.7		Ω
Diode Forward Voltage	V_{SD}	I_S=20A,V_{GS}=0V		0.9	1.2	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=75V,V_{GS}=10V I_D=20A		66		nC
Gate-Source Charge	Q_{gs}			11		
Gate-Drain Charge	Q_{gd}			24		
Input Capacitance	C_{iss}	V_{DS}=75V,V_{GS}=0V f=1MHz		4770		pF
Output Capacitance	C_{oss}			340		
Reverse Transfer Capacitance	C_{rss}			92		
Turn-On Time	$t_{d(on)}$	V_{DD}=75V,V_{GS}=10V I_D=20A, R_G=10Ω		17		nS
	t_r			56		
Turn-Off Time	$t_{d(off)}$			30		
	t_f			28		

TYPICAL CHARACTERISTICS

Fig 1. Typical Output Characteristics

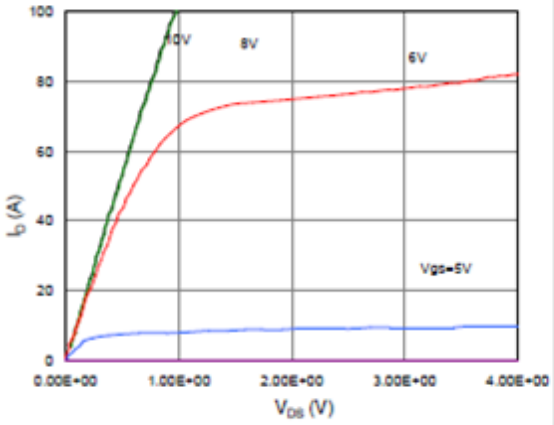


Figure 2. On-Resistance vs. Gate-Source Voltage

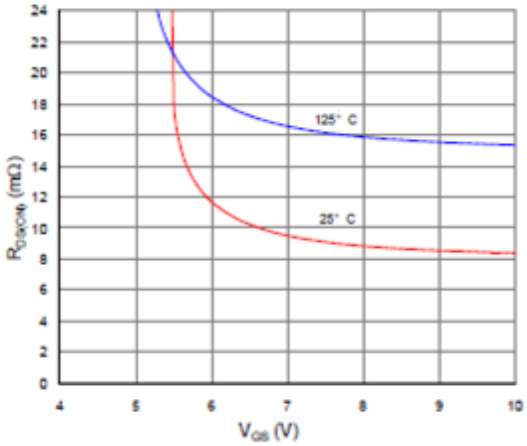


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

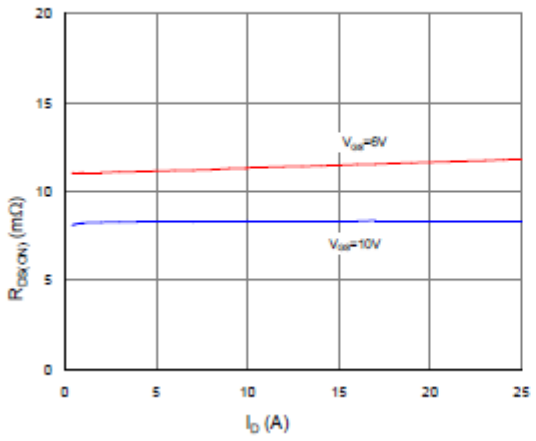


Figure 4. Normalized On-Resistance vs. Junction Temperature

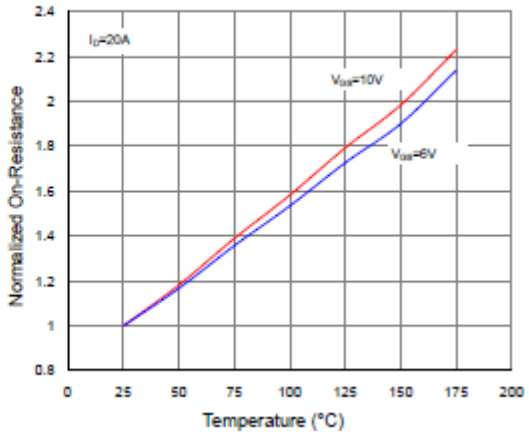


Figure 5. Typical Transfer Characteristics

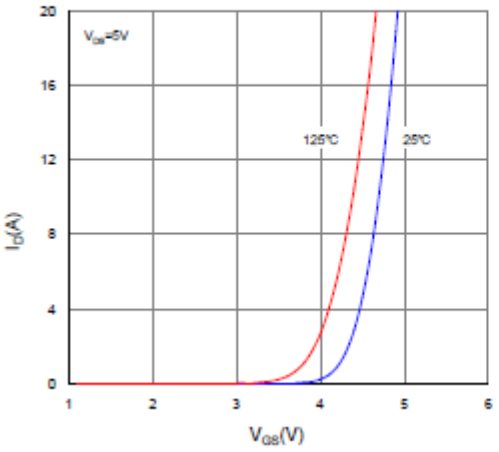
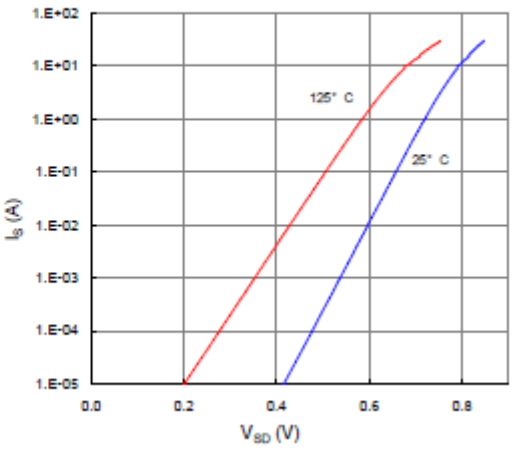


Figure 6. Typical Source-Drain Diode Forward Voltage



TYPICAL CHARACTERISTICS

Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

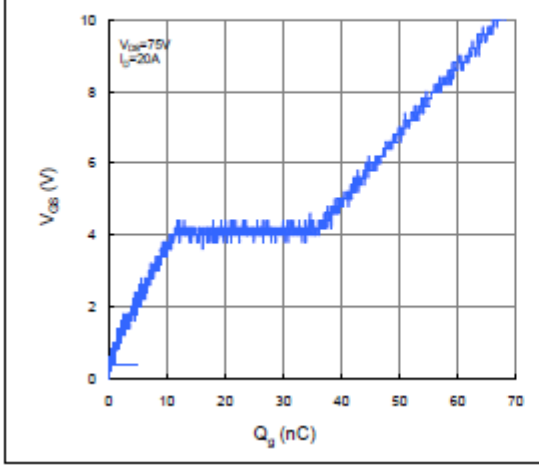


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

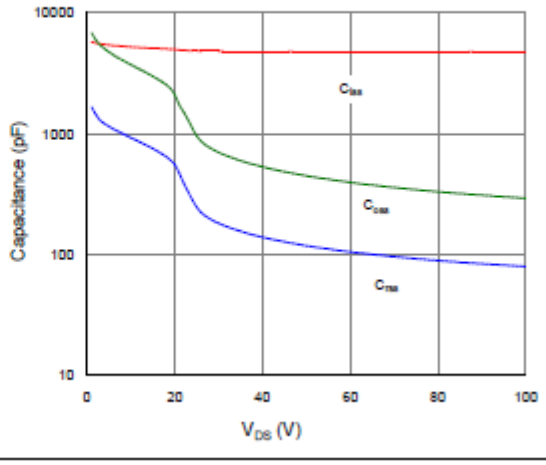


Figure 9. Maximum Safe Operating Area

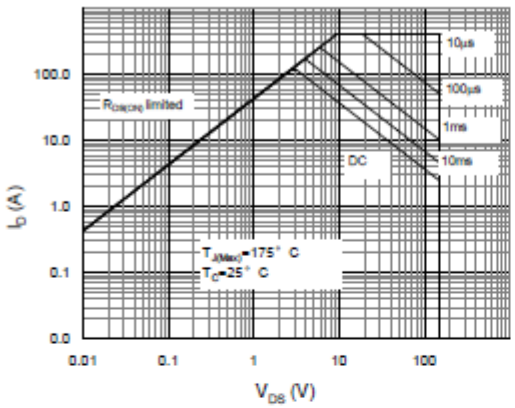


Figure 10. Maximun Drain Current vs. Case Temperature

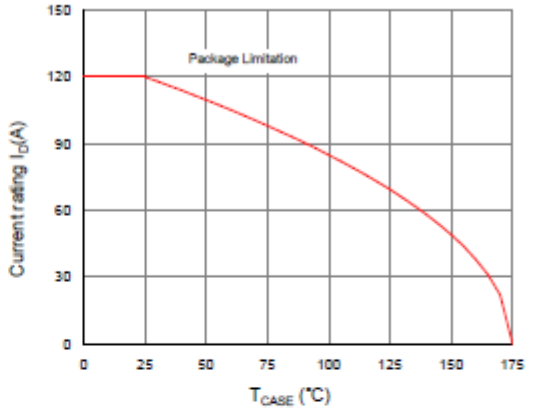
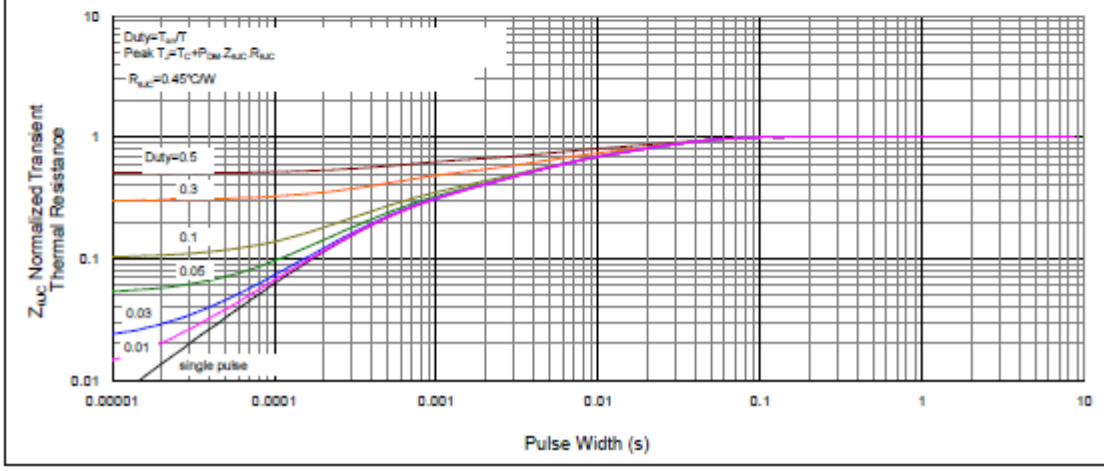


Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Case



SYNC Power Corporation
7F-2, No.3-1, Park Street
NanKang District (NKSP), Taipei, Taiwan 115
Phone: 886-2-2655-8178
Fax: 886-2-2655-8468
© http://www.syncpower.com